RENESAS

HD74HC323

8-bit Universal Shift/Storage Register (with 3-state Outputs)

REJ03D0610-0200 (Previous ADE-205-489) Rev.2.00 Jan 31, 2006

Description

This eight-bit universal register features multiplexed I/O ports to achieve full eight bit data handling in a single 20-pin package. HD74HC323 applications are as stacked or push-down registers, buffer storage, and accumulator registers.

Two function-select inputs and two output control inputs can be used to choose the modes of operation listed in the function table.

Synchronous parallel loading is accomplished by taking both function-select lines S_0 and S_1 high. This places the threestate outputs in a high-impedance state, which permits data that is applied on the I/O ports to be clocked into the register. Reading out of this register can be accomplished while the outputs are enabled in any mode. The clear function is synchronous, and a low level at the clear input clears the register on the next low-to-high transition of the clock.

Features

- High Speed Operation: t_{pd} (Clock to Q) = 20 ns typ (C_L = 50 pF)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 2 \text{ to } 6 \text{ V}$
- Low Input Current: 1 µA max
- Low Quiescent Supply Current: I_{CC} (static) = 4 μ A max (Ta = 25°C)
- Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74HC323RPEL	SOP-20 pin (JEDEC)	PRSP0020DC-A (FP-20DBV)	RP	EL (1,000 pcs/reel)

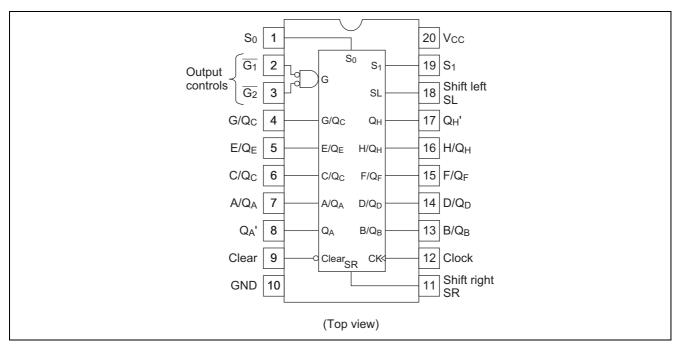
Function Table

				Inp	uts													
Mode	Clear	Fund Sel	ction ect	Out Cor	put trol	Clock	Se	rial	Inputs/Outputs								Outputs	
		S ₁	So	<u>G</u> ₁†	<u></u> G₂†		S∟	S _R	A/Q _A	B/Q _B	C/Q _c	D/Q _D	E/Q _E	F/Q _F	G/Q_G	H/Q _H	Q _A '	Q _H '
Clear	L	Х	L	L	L		Х	Х	L	L	L	L	L	L	L	L	L	L
	L	L	Х	L	L		Х	Х	L	L	L	L	L	L	L	L	L	L
Hold	Н	L	L	L	L	Х	Х	Х	Q _{A0}	Q_{B0}	Q_{C0}	Q_{D0}	Q_{E0}	Q_{F0}	Q_{G0}	Q_{H0}	Q_{A0}	Q _{H0}
	Н	Х	Х	L	L	L	Х	Х	Q _{A0}	Q_{B0}	Q_{C0}	Q_{D0}	Q_{E0}	Q_{F0}	Q_{G0}	Q_{H0}	Q_{A0}	Q _{H0}
Shift	Н	L	Н	L	L		Х	Н	Н	\mathbf{Q}_{An}	Q_{Bn}	Q _{Cn}	Q_{Dn}	Q_{En}	Q_{Fn}	Q_{Gn}	Н	Q_{Gn}
Right	Н	L	Н	L	L		Х	L	L	\mathbf{Q}_{An}	Q_{Bn}	Q _{Cn}	Q_{Dn}	Q_{En}	Q_{Fn}	Q_{Gn}	L	Q_{Gn}
Shift	Н	Н	L	L	L		Н	Х	Q_{Bn}	Q_{Cn}	Q_{Dn}	Q_{En}	Q_{Fn}	Q_{Gn}	Q_{Hn}	Н	Q_{Bn}	Н
Left	Н	Н	L	L	L		L	Х	Q_{Bn}	Q _{Cn}	Q_{Dn}	Q_{En}	Q_{Fn}	Q_{Gn}	Q _{Hn}	L	Q_{Bn}	L
Load	Н	Н	Н	Х	Х		Х	Х	а	b	С	d	е	f	g	h	а	h

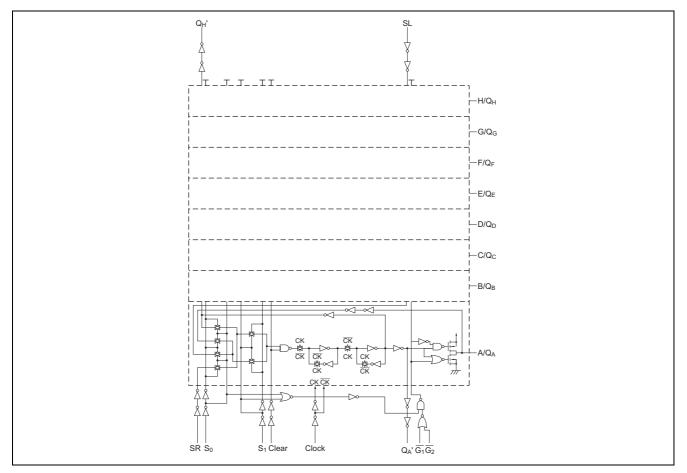
a ... h = the level of the steady-state input at A through H, respectively. These data are loaded into the flip-flops while the flip-flop outputs are isolated from the input/output terminals.



Pin Arrangement



Logic Diagram





Absolute Maximum Ratings

Item	Symbol	Ratings	Unit
Supply voltage range	V _{CC}	-0.5 to 7.0	V
Input / Output voltage	V _{IN} , V _{OUT}	–0.5 to V _{CC} +0.5	V
Input / Output diode current	I _{IK} , I _{OK}	±20	mA
Output current	I _{OUT}	±35	mA
V _{CC} , GND current	I _{CC} or I _{GND}	±75	mA
Power dissipation	PT	500	mW
Storage temperature	Tstg	-65 to +150	°C

Note: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

ltem	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{cc}	2 to 6	V	
Input / Output voltage	$V_{\text{IN}}, V_{\text{OUT}}$	0 to V _{CC}	V	
Operating temperature	Та	-40 to 85	°C	
		0 to 1000		V _{CC} = 2.0 V
Input rise / fall time ^{*1}	t _r , t _f	0 to 500	ns	V _{CC} = 4.5 V
		0 to 400		$V_{CC} = 6.0 V$

Note: 1. This item guarantees maximum limit when one input switches.

Electrical Characteristics

Itom	Symbol	V 00	Ta = 25°C			Ta = -40	to+85°C	11014	To al O an dition o		
ltem	Symbol	V _{cc} (V)	Min	Тур	Max	Min	Max	Unit	Test Conditions		
Input voltage	VIH	2.0	1.5		—	1.5		V			
		4.5	3.15		—	3.15					
		6.0	4.2		—	4.2					
	V _{IL}	2.0			0.5	—	0.5	V			
		4.5			1.35	—	1.35				
		6.0			1.8	—	1.8				
Output voltage	V _{OH}	2.0	1.9	2.0	—	1.9		V	$Vin = V_{IH} \text{ or } V_{IL}$	I _{OH} = -20 μA	
		4.5	4.4	4.5	—	4.4					
		6.0	5.9	6.0	—	5.9					
		4.5	4.18	_	—	4.13			Q _A to Q _H	I _{OH} = -6 mА	
		6.0	5.68	_	—	5.63				I _{OH} = -7.8 mA	
		4.5	4.18	_	_	4.13			Q _A ', Q _H '	$I_{OH} = -4 \text{ mA}$	
		6.0	5.68	_	—	5.63				$I_{OH} = -5.2 \text{ mA}$	
	V _{OL}	2.0	_	0.0	0.1	—	0.1	V	$Vin = V_{IH} \text{ or } V_{IL}$	I _{OL} = 20 μA	
		4.5	_	0.0	0.1	—	0.1				
		6.0	_	0.0	0.1	—	0.1				
		4.5	_	_	0.26	—	0.33		Q _A to Q _H	$I_{OL} = 6 \text{ mA}$	
		6.0	_	_	0.26	—	0.33			I _{OL} = 7.8 mA	
		4.5	_	_	0.26	—	0.33		Q _A ', Q _H '	$I_{OL} = 4 \text{ mA}$	
		6.0	_	_	0.26	—	0.33			I _{OL} = 5.2 mA	
Off-state output current	l _{oz}	6.0			±0.5	—	±5.0	μA	$Vin = V_{IH} \text{ or } V_{IL},$ $Vout = V_{CC} \text{ or } G$	ND	
Input current	lin	6.0	—		±0.1	_	±1.0	μA	Vin = V _{CC} or GND		
Quiescent supply current	lcc	6.0		_	4.0	—	40	μA	$Vin = V_{CC} \text{ or } GN$	ID, lout = 0 μA	

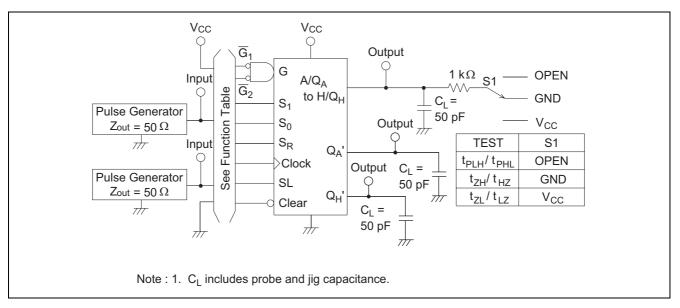


Switching Characteristics

 $(C_L = 50 \text{ pF}, \text{ Input } t_r = t_f = 6 \text{ ns})$

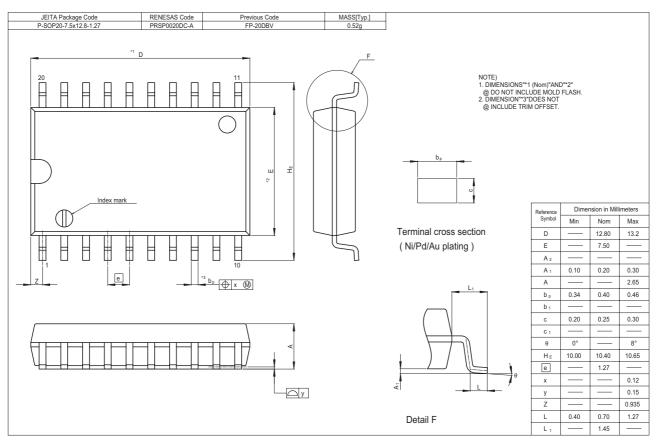
ltam	Symbol	v 00	Т	a = 25°	С	Ta = -40	to +85°C	Unit	Test Conditions	
Item	Symbol	V _{cc} (V)	Min	Тур	Max	Min	Max	Unit	Test Conditions	
Maximum clock	f _{max}	2.0	_	_	5	—	4	MHz		
frequency		4.5	_	—	27	_	21			
		6.0	_	_	31	_	24			
Propagation delay	t _{PLH}	2.0	_	_	150	_	190	ns	Clock to Q _A ' or Q _H '	
time	t _{PHL}	4.5	_	18	30	_	38			
		6.0	_	_	26	_	33			
		2.0	_	_	175	_	220	ns	Clock to Q	
		4.5	_	20	35	_	44			
		6.0	_	_	30	_	37			
Output enable time	t _{ZH}	2.0	_	—	150	—	190	ns		
	t _{ZL}	4.5	_	14	30	—	38			
		6.0	_	—	26	—	33			
Output disable	t _{HZ}	2.0	_	—	150	—	190	ns		
time	t _{LZ}	4.5	_	15	30	—	38			
		6.0		—	26	_	33			
Output rise/fall	t _{тLH}	2.0		—	75	_	95	ns	Q _A ', Q _H '	
time	t_{THL}	4.5		5	15	_	19			
		6.0		—	13	_	16			
		2.0		—	60		75	ns	Q	
		4.5		4	12	—	15			
		6.0	_	—	10		13			
Input capacitance	Cin	—	_	5	10	_	10	pF		

Test Circuit





Package Dimensions





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